

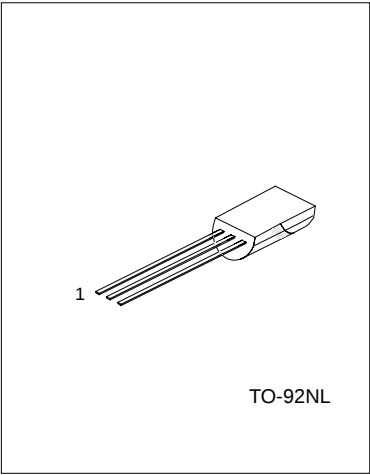
UTC 2SC2328A

NPN EPITAXIAL SILICON TRANSISTOR

AUDIO POWER AMPLIFIER

FEATURES

- *Collector Dissipation $P_c=1\text{ W}$
- *3 W Output Application
- *Complement of 2SA928A



1: EMITTER 2: COLLECTOR 3: BASE

ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CB0}	30	V
Collector-emitter voltage	V_{CE0}	30	V
Emitter-base voltage	V_{EB0}	5	V
Collector dissipation	P_c	1	W
Collector current	I_c	2	A
Junction Temperature	T_j	150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	BV_{CB0}	$I_c=100\mu A, I_E=0$	30			V
Collector-emitter breakdown voltage	BV_{CE0}	$I_c=10mA, I_B=0$	30			V
Emitter-base breakdown voltage	BV_{EB0}	$I_E=1mA, I_c=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=30V, I_E=0$			100	nA
Emitter cut-off current	I_{EBO}	$V_{BE}=5V, I_c=0$			100	nA
DC current gain(note)	h_{FE}	$V_{CE}=2V, I_c=500mA$	100		320	
Base-emitter on voltage	$V_{BE(on)}$	$V_{CE}=2V, I_c=500mA$			1	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c=1.5A, I_B=0.03A$			2	V
Output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		30		pF
Current gain bandwidth product	f_T	$V_{CE}=2V, I_c=500mA$		120		MHz

CLASSIFICATION OF h_{FE}

RANK	O	Y
RANGE	100-200	160-320

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TYPICAL CHARACTERISTIC CURVES

